

**AMENDMENTS TO THE CLAIMS**

Please amend the claims as follows:

1. (Currently amended) A semiconductor device comprising:

a single crystalline underlying layer formed in part of a substrate;

an insulating layer formed in another part of the substrate;

a semiconductor layer epitaxially grown above the underlying layer and having a composition represented by  $\text{Si}_{1-x_1-y_1}\text{Ge}_{x_1}\text{C}_{y_1}$  (where  $0 < x_1 < 1$ ,  $0 \leq y_1 < 1$ );

a buffer layer epitaxially grown between the underlying layer and the semiconductor layer and having a composition represented by  $\text{Si}_{1-x_2-y_2}\text{Ge}_{x_2}\text{C}_{y_2}$  (where  $0 \leq x_2 < 1$ ,  $0 \leq y_2 < 1$ ,  $1-x_2-y_2 > 1-x_1-y_1$ ); and

a polycrystalline semiconductor layer formed on the insulating layer and including a first semiconductor film having substantially the same composition as the buffer layer and a second semiconductor film having substantially the same composition as the semiconductor layer,

wherein the first semiconductor film has a thickness smaller than the buffer layer and the second semiconductor film has substantially the same thickness as the semiconductor layer.

2. (Original) The semiconductor device of claim 1, wherein the single crystalline underlying layer is a silicon layer.

3. (Original) The semiconductor device of claim 2, wherein the semiconductor layer is an SiGe layer or an SiGeC layer,

wherein the buffer layer is a silicon layer and

wherein the polycrystalline semiconductor layer contains at least SiGe.

4. (Original) The semiconductor device of claim 3, wherein the underlying layer is a collector layer,

wherein the semiconductor layer has at least part serving as a base layer and

wherein the polycrystalline semiconductor layer serves as at least part of a base lead-electrode,

the semiconductor device functioning as a heterojunction bipolar transistor.

5. (Original) The semiconductor device of claim 4, wherein the polycrystalline semiconductor layer serves as at least part of a gate electrode of an MIS transistor,

the semiconductor device functioning as a BiCMOS device.

6. (Original) The semiconductor device of claim 1, wherein the buffer layer has a thickness of not less than 2 nm nor more than 20 nm.

7-16. (Cancelled)

17. (New) The semiconductor device of claim 1, further comprising a polycrystalline silicon film covering the polycrystalline semiconductor layer.

18. (New) The semiconductor device of claim 17, wherein the polycrystalline silicon film is connected to the semiconductor layer at an edge of the polycrystalline semiconductor layer.

19. (New) The semiconductor device of claim 18, further comprising a sidewall formed on each side wall of the polycrystalline silicon film, the sidewall being composed of an oxide film or a nitride film.